

# TRANSISTOR(PNP)

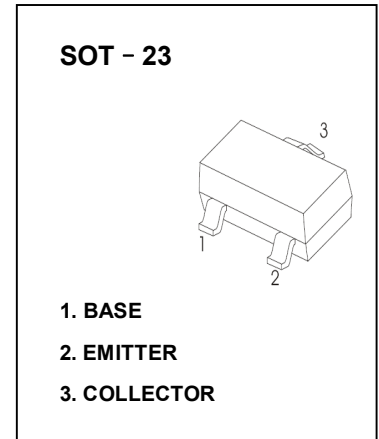
## FEATURES

- For Applications Requiring High Current Gain

**MARKING:2V**

## MAXIMUM RATINGS ( $T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{CB0}$	Collector-Base Voltage	-30	V
$V_{CEO}$	Collector-Emitter Voltage	-30	V
$V_{EBO}$	Emitter-Base Voltage	-10	V
$I_C$	Collector Current	-800	mA
$P_C$	Collector Power Dissipation	300	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	416	$^{\circ}\text{C}/\text{W}$
$T_j$	Junction Temperature	150	$^{\circ}\text{C}$
$T_{stg}$	Storage Temperature	-55~+150	$^{\circ}\text{C}$



## ELECTRICAL CHARACTERISTICS ( $T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CB0}$	$I_C=-100\mu\text{A}, I_E=0$	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu\text{A}, I_C=0$	-10			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=-30\text{V}, I_E=0$			-0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=-10\text{V}, I_C=0$			-0.1	$\mu\text{A}$
DC current gain	$h_{FE(1)}$ *	$V_{CE}=-5\text{V}, I_C=-10\text{mA}$	10			K
	$h_{FE(2)}$ *	$V_{CE}=-5\text{V}, I_C=-100\text{mA}$	20			K
Collector-emitter saturation voltage	$V_{CE(sat)}$ *	$I_C=-100\text{mA}, I_B=-0.1\text{mA}$			-1.5	V
Base-emitter voltage	$V_{BE}$ *	$V_{CE}=-5\text{V}, I_C=-100\text{mA}$			-2	V
Transition frequency	$f_T$	$V_{CE}=-5\text{V}, I_C=-10\text{mA}, f=100\text{MHz}$	125			MHz

\*Pulse test: pulse width  $\leq 300\mu\text{s}$ , duty cycles  $\leq 2.0\%$ .